

NPN LOW POWER SILICON TRANSISTOR

Qualified per MIL-PRF-19500/ 182

Devices

2N720A

**2N1893
2N1893S**

Qualified Level

**JAN
JANTX
JANTXV**

MAXIMUM RATINGS

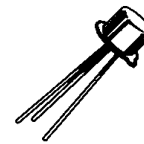
Ratings	Symbol	All Devices		Units
Collector-Emitter Voltage	V_{CEO}	80		Vdc
Collector-Base Voltage	V_{CBO}	120		Vdc
Emitter-Base Voltage	V_{EBO}	7.0		Vdc
Collector-Emitter Voltage ($R_{BE} = 10 \Omega$)	V_{CER}	100		Vdc
Collector Current	I_C	500		mAdc
		2N720A	2N1893, S	
Total Power Dissipation @ $T_A = +25^\circ\text{C}$ ⁽¹⁾ @ $T_C = +25^\circ\text{C}$ ⁽²⁾	P_T	0.5	0.8	W
		1.8	3.0	
Operating & Storage Junction Temperature Range	T_J, T_{srg}	-65 to +200		$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristics	Symbol	2N720A	2N1893, S	Unit
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	97	58	$^\circ\text{C/W}$

1) Derate linearly 2.86 mW/ $^\circ\text{C}$ for 2N720A, 4.57 mW/ $^\circ\text{C}$ for 2N1893, S $T_A > 25^\circ\text{C}$

2) Derate linearly 10.3 mW/ $^\circ\text{C}$ for 2N720A, 17.2 mW/ $^\circ\text{C}$ for 2N1893, S $T_C > 25^\circ\text{C}$



**TO-18 (TO-206AA)*
2N720A**



**TO-5*
2N1893, 2N1893S**

*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristics	Symbol	Min.	Max.	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage $I_C = 30 \text{ mAdc}$	$V_{(BR)CEO}$	80		Vdc
Collector-Emitter Breakdown Voltage $I_C = 10 \text{ mAdc}, R_{BE} = 10 \Omega$	$V_{(BR)CER}$	100		Vdc
Collector-Base Cutoff Current $V_{CB} = 120 \text{ Vdc}$ $V_{CB} = 90 \text{ Vdc}$	I_{CBO}		10 10	μAdc ηAdc
Emitter-Base Cutoff Current $V_{EB} = 7.0 \text{ Vdc}$ $V_{EB} = 5.0 \text{ Vdc}$	I_{EBO}		10 10	μAdc ηAdc

ELECTRICAL CHARACTERISTICS (con't)

Characteristics	Symbol	Min.	Max.	Unit
ON CHARACTERISTICS ⁽³⁾				
Forward-Current Transfer Ratio I _C = 0.1 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 10 mA _{dc} , V _{CE} = 10 V _{dc} I _C = 150 mA _{dc} , V _{CE} = 10 V _{dc}	h _{FE}	20 35 40	120	
Collector-Emitter Saturation Voltage I _C = 150 mA _{dc} , I _B = 15 mA _{dc}	V _{CE(sat)}		5.0	V _{dc}
Base-Emitter Voltage I _C = 150 mA _{dc} , I _B = 15 mA _{dc}	V _{BE(sat)}		1.3	V _{dc}

DYNAMIC CHARACTERISTICS

Magnitude of Common Emitter Small-Signal Short-Circuit Forward Current Transfer Ratio I _C = 50 mA _{dc} , V _{CE} = 10 V _{dc} , f = 20 MHz	h _{fe}	3.0	10	
Small-Signal Short-Circuit Forward Current Transfer Ratio V _{CE} = 5.0 V _{dc} , I _C = 1.0 mA _{dc} V _{CE} = 10 V _{dc} , I _C = 5.0 mA _{dc} , f = 1.0 kHz	h _{fe}	35 45	100	
Small-Signal Short-Circuit Input Impedance V _{CB} = 10 V _{dc} , I _C = 5.0 mA _{dc}	h _{ib}	4.0	8.0	Ω
Small-Signal Short-Circuit Output Admittance V _{CB} = 10 V _{dc} , I _C = 5.0 mA _{dc}	h _{ob}		0.5	μΩ
Output Capacitance V _{CB} = 10 V _{dc} , I _E = 0, 100 kHz ≤ f ≤ 1.0 MHz	C _{obo}	2	15	pF

SWITCHING CHARACTERISTICS

Turn-On Time + Turn-Off Time (See Figure 3 of MIL-PRF-19500/182)	t _{on} + t _{off}		30	ns
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(3) Pulse Test: Pulse Width = 300μs, Duty Cycle ≤ 2.0%.